

Digital transistor (built-in resistor)

DTA125TUA / DTA125TKA / DTA125TSA

●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making device design easy.
- 4) Higher mounting densities can be achieved.

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CE0}	-50	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	200 300	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

●Package, marking, and packaging specifications

Part No.	DTA125TUA	DTA125TKA	DTA125TSA
Package	UMT3	SMT3	SPT
Marking	9A	9A	-
Packaging code	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	5000

●External dimensions (Units : mm)

DTA125TUA

Each lead has same dimensions

ROHM : UMT3
EIAJ : SC-70

(1) Emitter(Source)
(2) Base(Gate)
(3) Collector(Drain)

DTA125TKA

Each lead has same dimensions

ROHM : SMT3
EIAJ : SC-59

(1) Emitter(Source)
(2) Base(Gate)
(3) Collector(Drain)

DTA125TSA

Taping specifications

ROHM : SPT
EIAJ : SC-72

(1) Emitter
(2) Collector
(3) Base

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-50	-	-	V	I _C = -50μA
Collector-emitter breakdown voltage	BV _{CE0}	-50	-	-	V	I _C = -1mA
Emitter-base breakdown voltage	BV _{EB0}	-5	-	-	V	I _E = -50μA
Collector cutoff current	I _{CB0}	-	-	-0.5	μA	V _{CB} = -50V
Emitter cutoff current	I _{EB0}	-	-	-0.5	μA	V _{EB} = -4V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	-0.3	V	I _C = -0.5mA, I _E = -0.05mA
DC current transfer ratio	h _{FE}	100	250	600	-	I _C = -1mA, V _{CE} = -5V
Input resistance	R _I	140	200	260	kΩ	-
Transition frequency	f _T	-	250	-	MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz *

* Transition frequency of the device.

●Circuit schematic

